FIG. 1

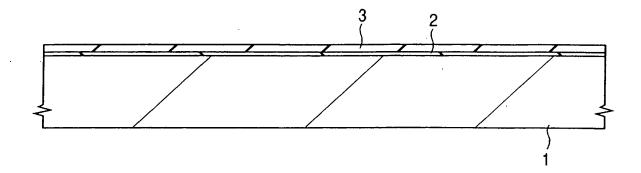
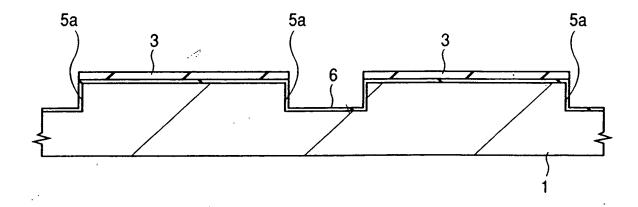


FIG. 2

FIG. 3



0)

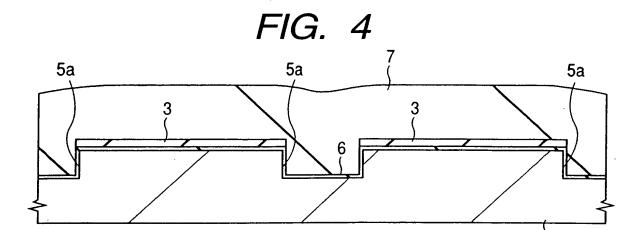


FIG. 5

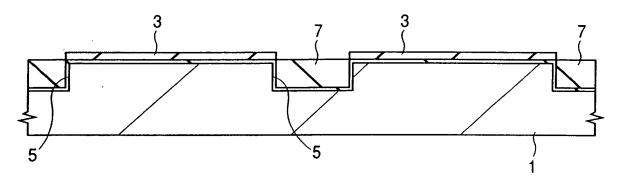


FIG. 6

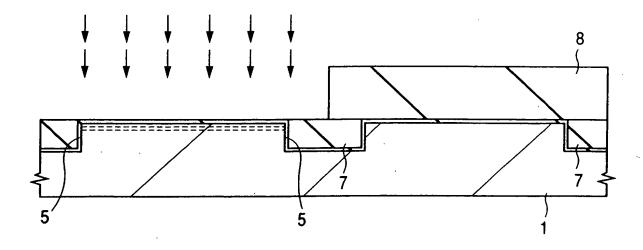


FIG. 7

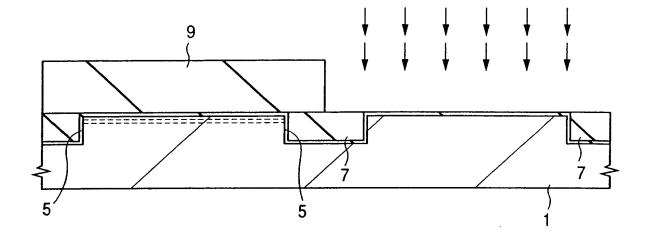


FIG. 8

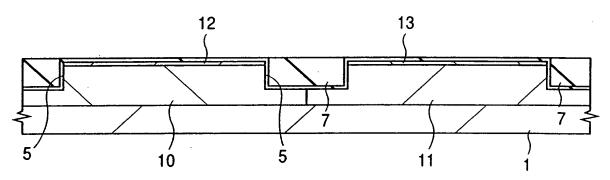
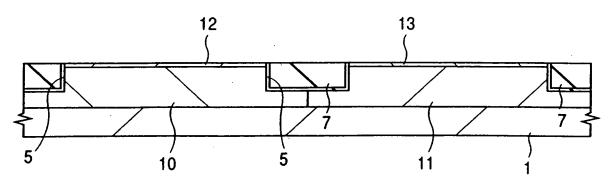
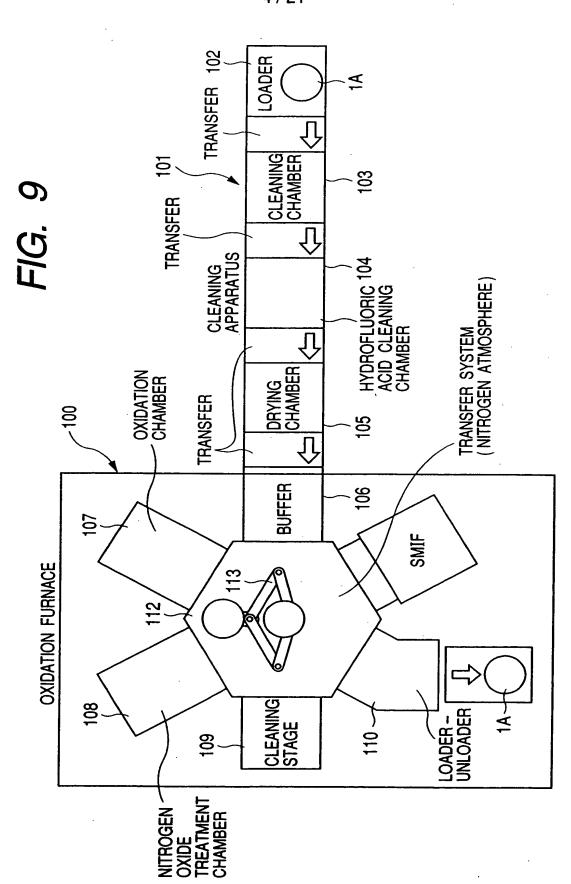


FIG. 10

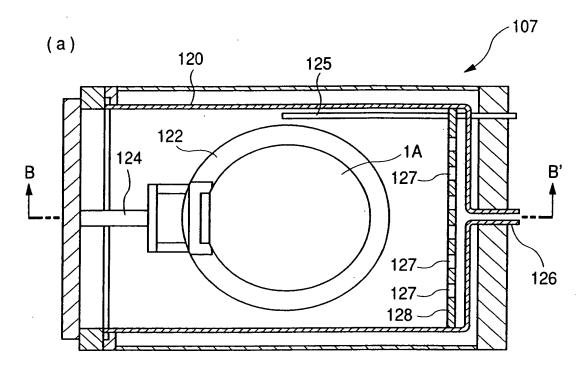


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FIG. 11



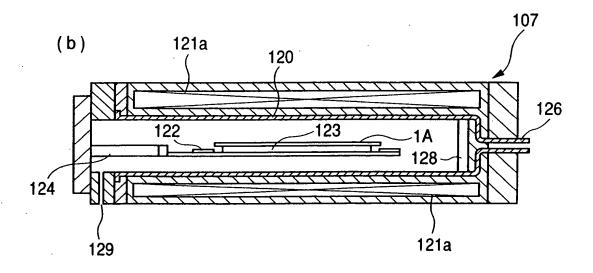
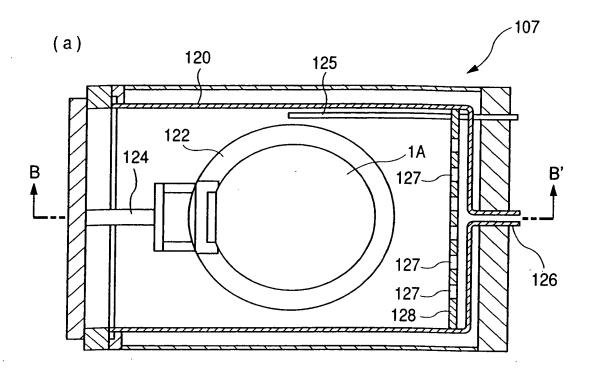
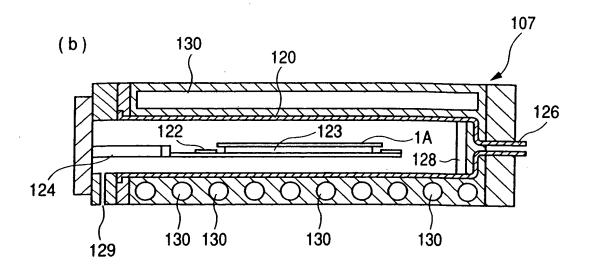
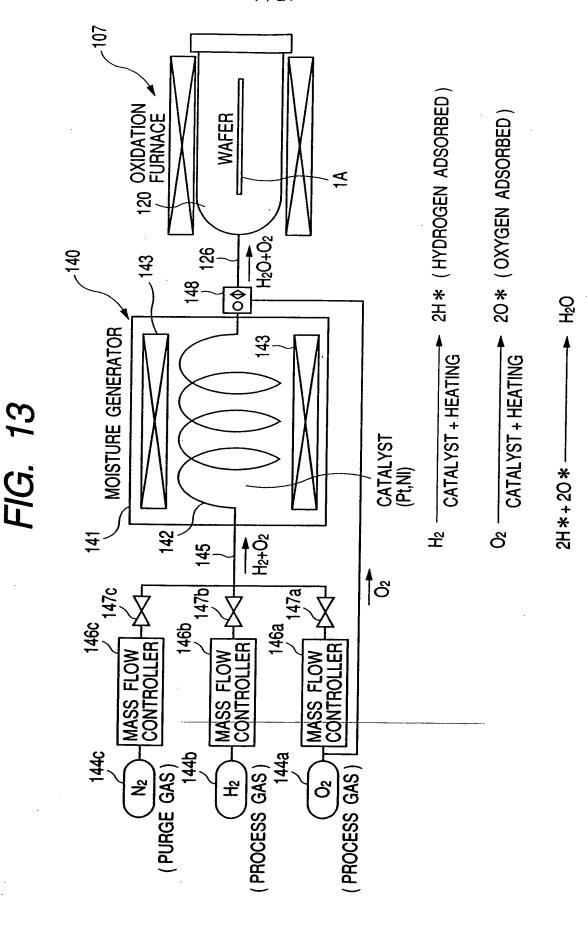


FIG. 12







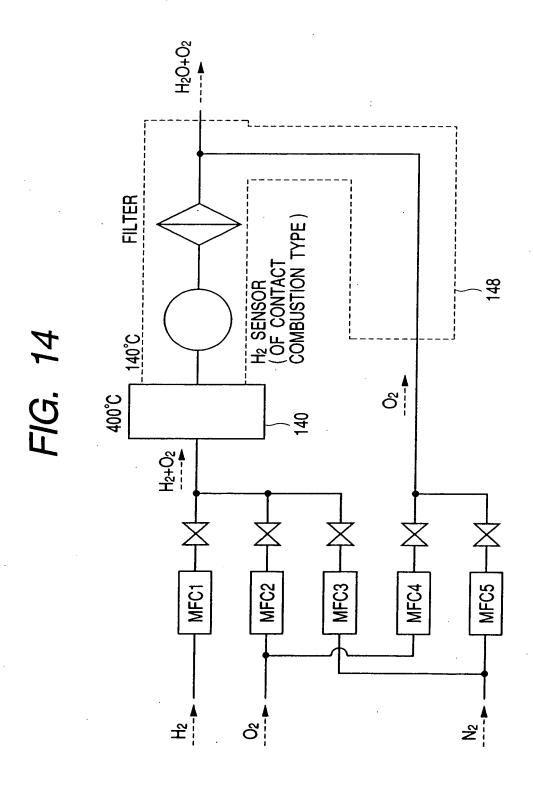


FIG. 15	WAFER	55,,		,		•		1, 1	
	AFTER- PURGE	2' 20''							
	OXIDATION	ດໃ							
	H <sub>2</sub> INTRODUCTION	15"							
	O <sub>2</sub> PURGE	0 – 55"							
	N <sub>2</sub> PURGE	1,							
	WAFER LOAD	55"							
		TIME	2	FLOW	O <sub>2</sub> FLOW RATE		H <sub>2</sub> FLOW RATE		

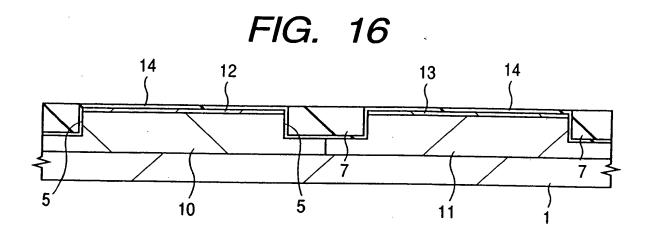
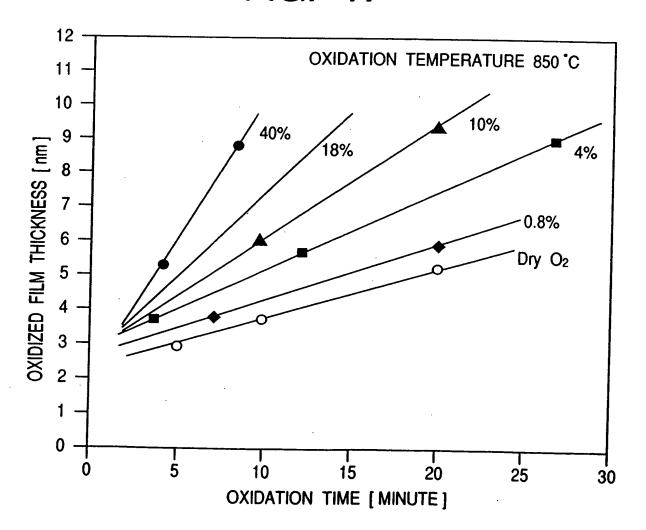
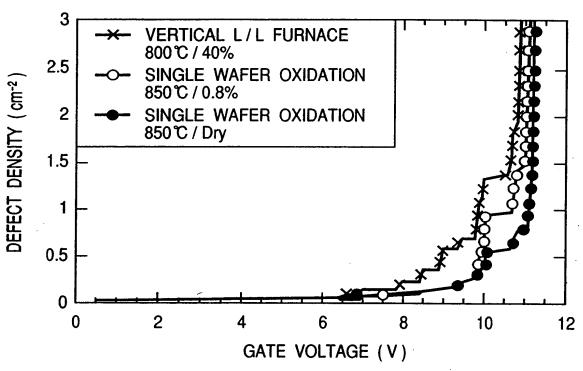


FIG. 17

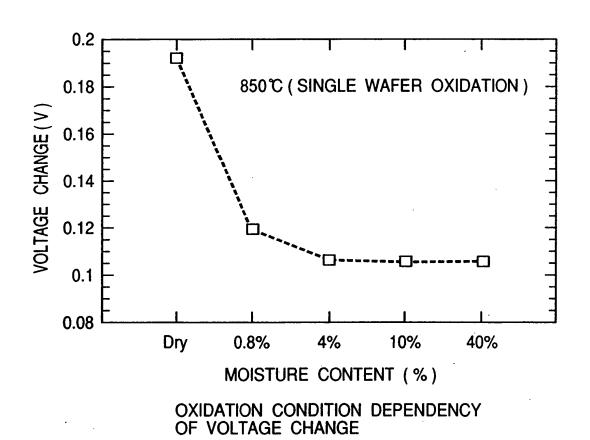


## FIG. 18



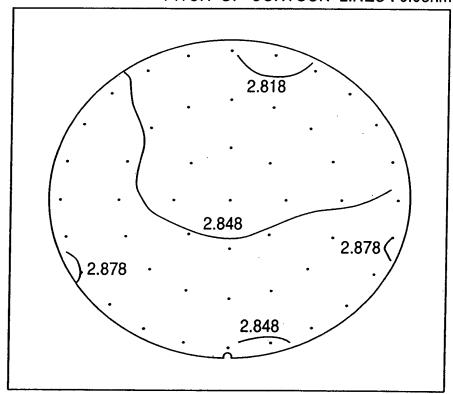
INITIAL WITHSTAND VOLTAGE OF LOW MOISTURE CONTENT OXIDE FILM (OXIDE FILM THICKNESS =  $9nm,S = 0.19cm^2$ )

FIG. 19



## FIG. 20





WAFER DIAMETER: 8 inch

AVERAGE: 2.848 [ nm ]

MAX.: 2.881 [ nm ]

MIN.: 2.814 [ nm ] MAX. – MIN.: 0.067 [ nm ]

. . 0.067 [ 11111 ] . ±1.18 [ .% ]

TREATING CONDITIONS: 850°C, 2'30"

H<sub>2</sub> / O<sub>2</sub>: 0.05 / 4.9slm (MOISTURE CONTENT: 0.8%)

MEASUREMENT: AT 49 POINTS BY ELLIPSOMETER

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## FIG. 21

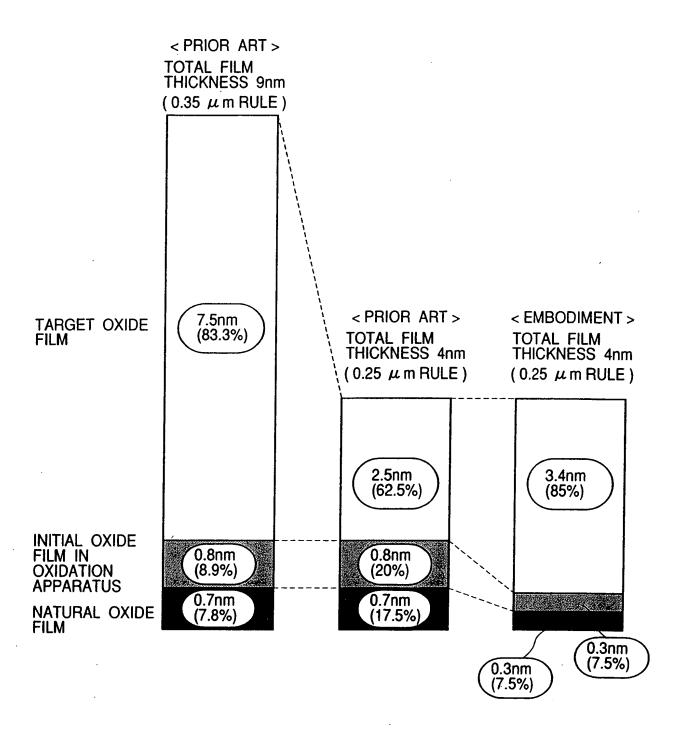


FIG. 22

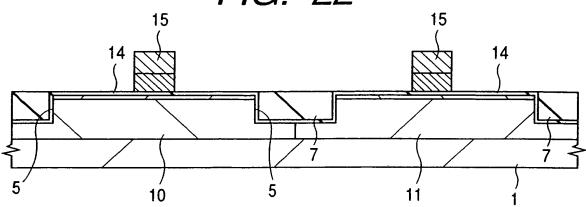


FIG. 23

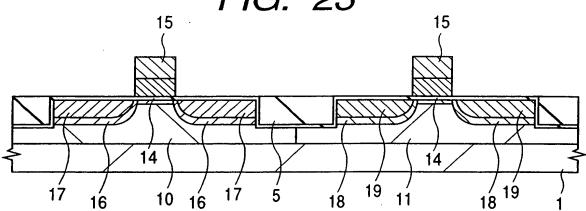


FIG. 24

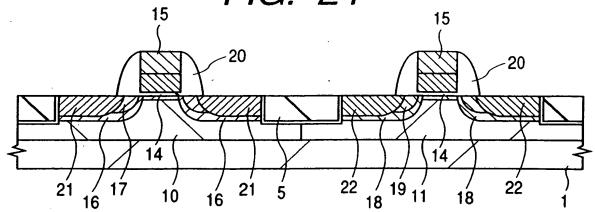


FIG. 25

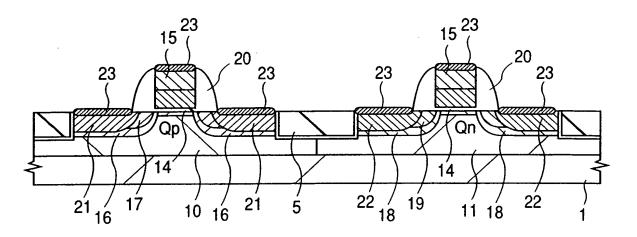


FIG. 26

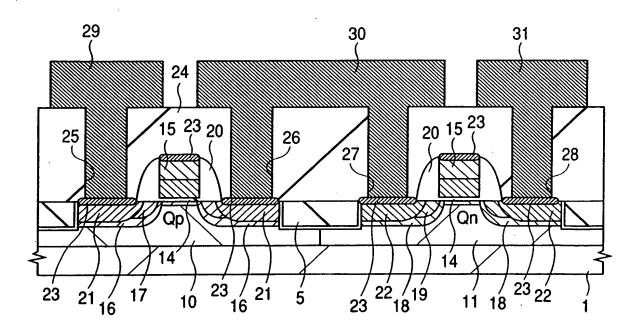


FIG. 27

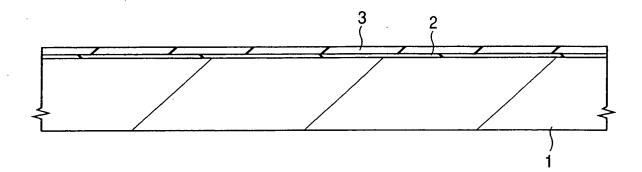


FIG. 28

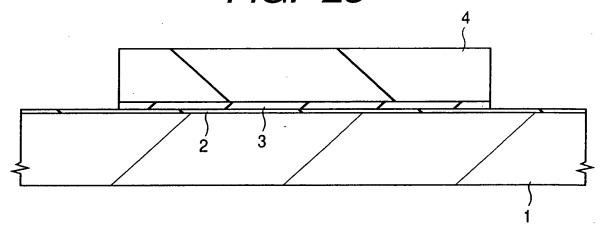


FIG. 29

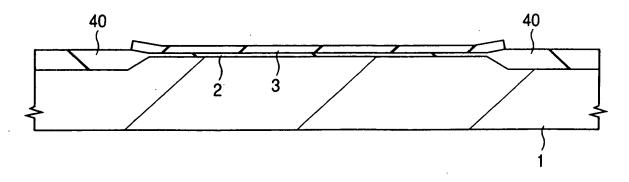
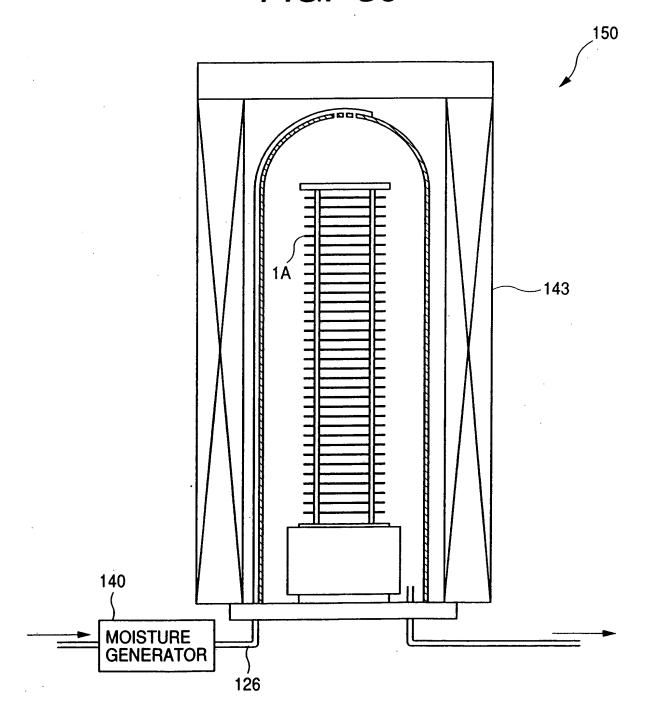


FIG. 30



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WAFER UNLOAD <del>.</del> AFTER-Purge 2, 20,, ARBITRARY (SEVERAL MINS.) OXIDATION FIG. 31 H<sub>2</sub> INTRODUCTION 5 O<sub>2</sub> Purge ີ່ຄ N<sub>2</sub> Purge WAFER LOAD 9 TIME N<sub>2</sub> FLOW RATE O<sub>2</sub> FLOW RATE H2 FLOW RATE

()()

FIG. 32

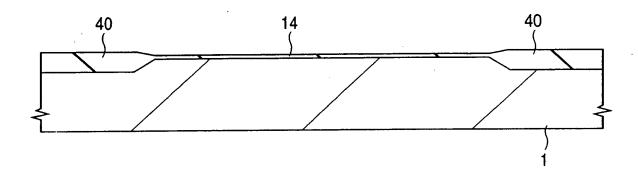
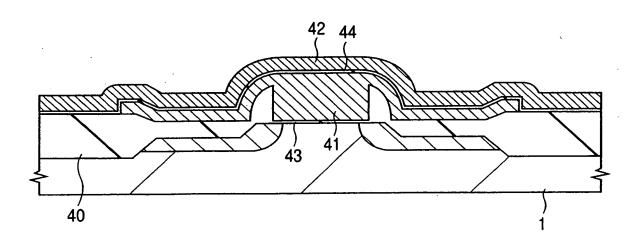


FIG. 34



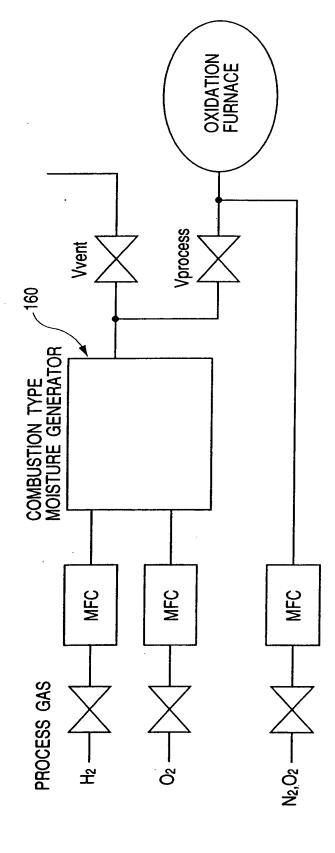


FIG. 33